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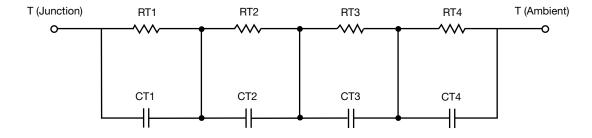
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



C VALUES FOR TANK	C VALUES FOR TANK CONFIGURATION				
	THERMAL RES	ISTANCE (°C/W)			
Junction to	Ambient	Case	Foot		
RT1	11.9104	56.0108m	N/A		
RT2	3.1921	118.3244m	N/A		
RT3	931.0189m	98.8039m	N/A		
RT4	23.9695	126.8609m	N/A		
	THERMAL CAPAC	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	8.2562	81.2261m	N/A		
CT2	1.0641	73.2803m	N/A		
СТЗ	147.3202m	7.4826m	N/A		
CT4	4.0108	326.7892m	N/A		

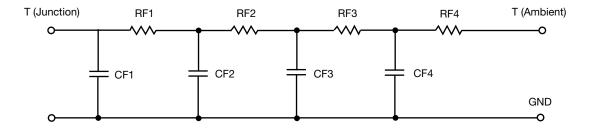
Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	884.7234m	104.1226m	N/A		
RF2	6.5762	119.5530m	N/A		
RF3	23.1425	160.4529m	N/A		
RF4	9.4830	15.8715m	N/A		
	THERMAL CAPACI	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	24.3391m	6.0641m	N/A		
CF2	882.6174m	11.2842m	N/A		
CF3	1.7594	131.0053m	N/A		
CF4	2.6137	1.2391	N/A		

Note

• n/a indicates not applicable





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